



# BYT11-600 - BYT11-1000

## HIGH EFFICIENCY RECTIFIER DIODES

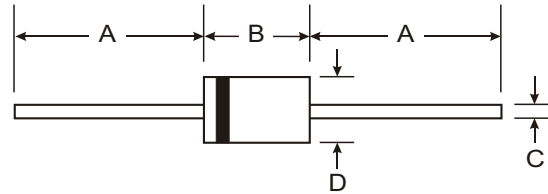
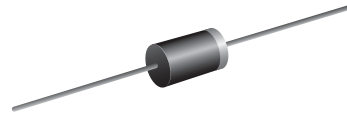
**VOLTAGE RANGE: 600 - 1000V**  
**CURRENT: 1.0 A**

### Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

### Mechanical Data

- Case: DO-41 Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-41 Plastic		
Dim	Min	Max
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

### Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	BYT11-600	BYT11-800	BYT11-1000	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$	600	800	1000	V
Working Peak Reverse Voltage	$V_{RWM}$				
DC Blocking Voltage	$V_R$				
RMS Reverse Voltage	$V_{R(RMS)}$	420	560	700	V
Average Rectified Output Current (Note 1) $@T_A = 55^\circ\text{C}$	$I_o$	1.0			A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	20			A
Forward Voltage $@I_F = 1.0\text{A}$	$V_{FM}$	1.3			V
Peak Reverse Current $@T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage $@T_A = 100^\circ\text{C}$	$I_{RM}$	20			$\mu\text{A}$
Reverse Recovery Time (Note 2)	$t_{rr}$	100			nS
Typical Junction Capacitance (Note 3)	$C_j$	15			pF
Operating Temperature Range	$T_j$	-65 to +125			$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-65 to +150			$^\circ\text{C}$

- Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case  
 2. Measured with  $I_F = 0.5\text{A}$ ,  $I_R = 1.0\text{A}$ ,  $I_{RR} = 0.25\text{A}$ . See figure 5.  
 3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.